



# Thyristor

$V_{RRM} = 1600\text{ V}$

$I_{TAV} = 30\text{ A}$

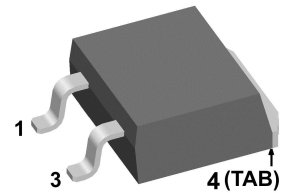
$V_T = 1.96\text{ V}$

## SemiFast Single Thyristor

### Part number

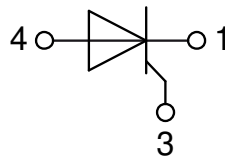
**CME30E1600PZ**

Marking on Product: CME30E1600PZ



Backside: anode

ESD Level: H3B



### Features / Advantages:

- Thyristor for line and moderate frequencies
- Short turn-off time
- Planar passivated chip
- Long-term stability

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-263 (D2Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

### Disclaimer Notice

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| Thyristor      |  |  | Ratings                 |      |      |                  |
|----------------|--|--|-------------------------|------|------|------------------|
| Symbol         | Definition   | Conditions   | min.                    | typ. | max. | Unit             |
| $V_{RSM/DSM}$  | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$   |                         |      | 1700 | V                |
| $V_{RRM/DRM}$  | max. repetitive reverse/forward blocking voltage     | $T_{VJ} = 25^{\circ}C$   |                         |      | 1600 | V                |
| $I_{RD}$       | reverse current, drain current                       | $V_{R/D} = 1600 V$   | $T_{VJ} = 25^{\circ}C$  |      | 50   | $\mu A$          |
|                |  | $V_{R/D} = 1600 V$   | $T_{VJ} = 125^{\circ}C$ |      | 2    | mA               |
| $V_T$          | forward voltage drop                                 | $I_T = 30 A$   | $T_{VJ} = 25^{\circ}C$  |      | 1.92 | V                |
|                |  | $I_T = 60 A$   |                         |      | 2.47 | V                |
|                |  | $I_T = 30 A$   | $T_{VJ} = 125^{\circ}C$ |      | 1.96 | V                |
|                |  | $I_T = 60 A$   |                         |      | 2.68 | V                |
| $I_{TAV}$      | average forward current                              | $T_C = 80^{\circ}C$<br>180° sine   | $T_{VJ} = 150^{\circ}C$ |      | 30   | A                |
| $V_{T0}$       | threshold voltage                                    | } for power loss calculation only  | $T_{VJ} = 150^{\circ}C$ |      | 1.23 | V                |
| $r_T$          | slope resistance                                     |  |                         |      | 25   | m $\Omega$       |
| $R_{thJC}$     | thermal resistance junction to case                  |  |                         |      | 0.75 | K/W              |
| $R_{thCH}$     | thermal resistance case to heatsink                  |  |                         | 0.25 |      | K/W              |
| $P_{tot}$      | total power dissipation                              |  | $T_C = 25^{\circ}C$     |      | 165  | W                |
| $I_{TSM}$      | max. forward surge current                           | $t = 10 ms$ ; (50 Hz), sine  | $T_{VJ} = 45^{\circ}C$  |      | 260  | A                |
|                |  | $t = 8,3 ms$ ; (60 Hz), sine   | $V_R = 0 V$             |      | 280  | A                |
|                |  | $t = 10 ms$ ; (50 Hz), sine  | $T_{VJ} = 150^{\circ}C$ |      | 220  | A                |
|                |  | $t = 8,3 ms$ ; (60 Hz), sine   | $V_R = 0 V$             |      | 240  | A                |
| $I^2t$         | value for fusing                                     | $t = 10 ms$ ; (50 Hz), sine  | $T_{VJ} = 45^{\circ}C$  |      | 340  | A <sup>2</sup> s |
|                |  | $t = 8,3 ms$ ; (60 Hz), sine   | $V_R = 0 V$             |      | 325  | A <sup>2</sup> s |
|                |  | $t = 10 ms$ ; (50 Hz), sine  | $T_{VJ} = 150^{\circ}C$ |      | 240  | A <sup>2</sup> s |
|                |  | $t = 8,3 ms$ ; (60 Hz), sine   | $V_R = 0 V$             |      | 240  | A <sup>2</sup> s |
| $C_J$          | junction capacitance                                 | $V_R = 400 V$ $f = 1 MHz$  | $T_{VJ} = 25^{\circ}C$  |      | 13   | pF               |
| $P_{GM}$       | max. gate power dissipation                          | $t_p = 30 \mu s$   | $T_C = 150^{\circ}C$    |      | 10   | W                |
|                |  | $t_p = 300 \mu s$  |                         |      | 5    | W                |
| $P_{GAV}$      | average gate power dissipation                       |  |                         |      | 0.5  | W                |
| $(di/dt)_{cr}$ | critical rate of rise of current                     | $T_{VJ} = 125^{\circ}C$ ; $f = 50 Hz$ repetitive, $I_T = 90 A$   |                         |      | 150  | A/ $\mu s$       |
|                |  | $t_p = 200 \mu s$ ; $di_G/dt = 0.2 A/\mu s$ ;<br>$I_G = 0.2 A$ ; $V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 30 A$      |                         |      | 500  | A/ $\mu s$       |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage                     | $V = \frac{2}{3} V_{DRM}$<br>$R_{GK} = \infty$ ; method 1 (linear voltage rise)  | $T_{VJ} = 125^{\circ}C$ |      | 500  | V/ $\mu s$       |
| $V_{GT}$       | gate trigger voltage                                 | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$  |      | 1.3  | V                |
|                |  |  | $T_{VJ} = -40^{\circ}C$ |      | 1.6  | V                |
| $I_{GT}$       | gate trigger current                                 | $V_D = 6 V$  | $T_{VJ} = 25^{\circ}C$  |      | 50   | mA               |
|                |  |  | $T_{VJ} = -40^{\circ}C$ |      | 80   | mA               |
| $V_{GD}$       | gate non-trigger voltage                             | $V_D = \frac{2}{3} V_{DRM}$  | $T_{VJ} = 150^{\circ}C$ |      | 0.2  | V                |
| $I_{GD}$       | gate non-trigger current                             |  |                         |      | 1    | mA               |
| $I_L$          | latching current                                     | $t_p = 10 \mu s$   | $T_{VJ} = 25^{\circ}C$  |      | 120  | mA               |
|                |  | $I_G = 0.2 A$ ; $di_G/dt = 0.2 A/\mu s$  |                         |      |      |                  |
| $I_H$          | holding current                                      | $V_D = 6 V$ $R_{GK} = \infty$  | $T_{VJ} = 25^{\circ}C$  |      | 90   | mA               |
| $t_{gd}$       | gate controlled delay time                           | $V_D = \frac{1}{2} V_{DRM}$  | $T_{VJ} = 25^{\circ}C$  |      | 2    | $\mu s$          |
|                |  | $I_G = 0.5 A$ ; $di_G/dt = 0.5 A/\mu s$  |                         |      |      |                  |
| $t_q$          | turn-off time  | $V_R = 20 V$ ; $I_T = 30 A$ ; $V = \frac{2}{3} V_{DRM}$<br>$di/dt = 10 A/\mu s$ $dv/dt = 1000 V/\mu s$ $t_p = 200 \mu s$ | $T_{VJ} = 125^{\circ}C$ |      | 120  | $\mu s$          |



| Package TO-263 (D2Pak-HV) |  |                      | Ratings |      |      |      |
|---------------------------|--|----------------------|---------|------|------|------|
| Symbol                    | Definition   | Conditions           | min.    | typ. | max. | Unit |
| $I_{RMS}$                 | RMS current  | per terminal         |         |      | 35   | A    |
| $T_{VJ}$                  | virtual junction temperature                                 |                      | -40     |      | 150  | °C   |
| $T_{op}$                  | operation temperature  |                      | -40     |      | 125  | °C   |
| $T_{stg}$                 | storage temperature  |                      | -40     |      | 150  | °C   |
| <b>Weight</b>             |  |                      |         | 1.5  |      | g    |
| $F_C$                     | mounting force with clip                                     |                      | 20      |      | 60   | N    |
| $d_{Spp/App}$             | creepage distance on surface / striking distance through air | terminal to terminal | 4.2     |      |      | mm   |
| $d_{Spb/Apb}$             |  | terminal to backside | 4.7     |      |      | mm   |

**Product Marking**



**Part description**

- C = Thyristor (SCR)
- M = Thyristor
- E = Semifast (up to 1800V)
- 30 = Current Rating [A]
- E = Single Thyristor
- 1600 = Reverse Voltage [V]
- PZ = TO-263AB (D2Pak) (2HV)

| Ordering    | Ordering Number  | Marking on Product | Delivery Mode | Quantity | Code No. |
|-------------|------------------|--------------------|---------------|----------|----------|
| Standard    | CME30E1600PZ-TRL | CME30E1600PZ       | Tape & Reel   | 800      | 512781   |
| Alternative | CME30E1600PZ-TUB | CME30E1600PZ       | Tube          | 50       | 523828   |

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150\text{ °C}$



**Thyristor**

|              |                    |      |    |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage  | 1.23 | V  |
| $R_{0\ max}$ | slope resistance * | 22   | mΩ |

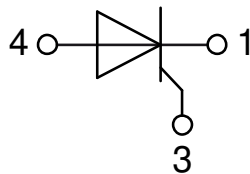


**Outlines TO-263 (D2Pak-HV)**



| Dim. | Millimeter |       | Inches      |       |
|------|------------|-------|-------------|-------|
|      | min        | max   | min         | max   |
| A    | 4.06       | 4.83  | 0.160       | 0.190 |
| A1   | typ. 0.10  |       | typ. 0.004  |       |
| A2   | 2.41       |       | 0.095       |       |
| b    | 0.51       | 0.99  | 0.020       | 0.039 |
| b2   | 1.14       | 1.40  | 0.045       | 0.055 |
| c    | 0.40       | 0.74  | 0.016       | 0.029 |
| c2   | 1.14       | 1.40  | 0.045       | 0.055 |
| D    | 8.38       | 9.40  | 0.330       | 0.370 |
| D1   | 8.00       | 8.89  | 0.315       | 0.350 |
| D2   | 2.3        |       | 0.091       |       |
| E    | 9.65       | 10.41 | 0.380       | 0.410 |
| E1   | 6.22       | 8.50  | 0.245       | 0.335 |
| e    | 2,54 BSC   |       | 0,100 BSC   |       |
| e1   | 4.28       |       | 0.169       |       |
| H    | 14.61      | 15.88 | 0.575       | 0.625 |
| L    | 1.78       | 2.79  | 0.070       | 0.110 |
| L1   | 1.02       | 1.68  | 0.040       | 0.066 |
| W    | typ. 0.02  | 0.040 | typ. 0.0008 | 0.002 |

*All dimensions conform with and/or within JEDEC standard.*



**Thyristor**

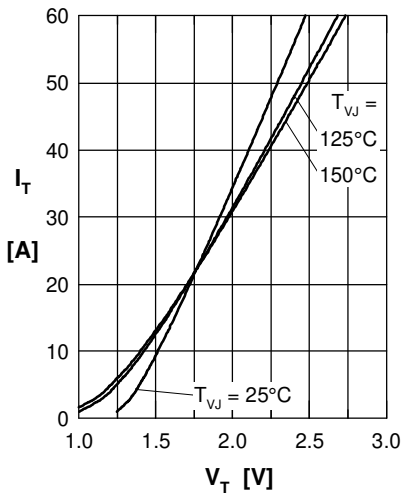


Fig. 1 Forward characteristics

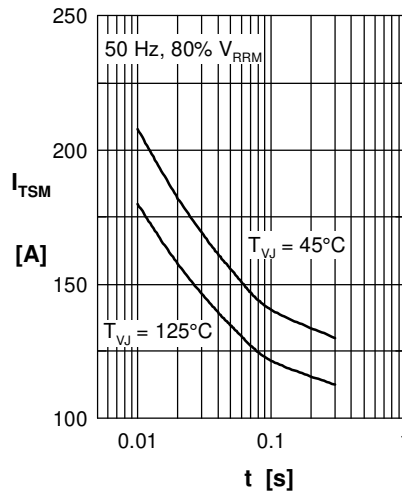


Fig. 2 Surge overload current  
 $I_{TSM}$ : crest value,  $t$ : duration

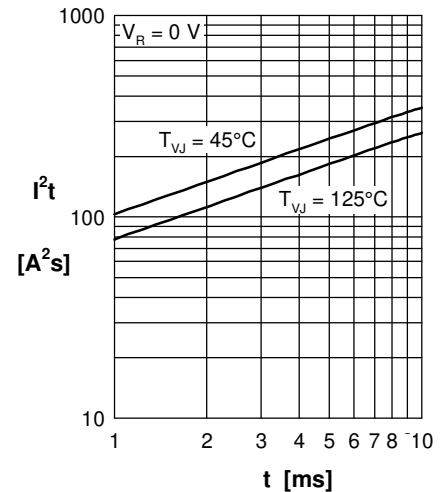


Fig. 3  $I^2t$  versus time (1-10 s)

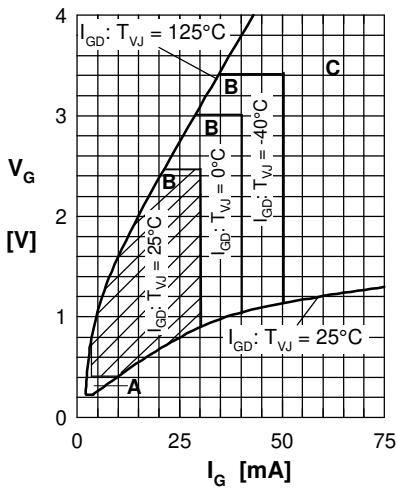


Fig. 4 Gate voltage & gate current  
Triggering: A = no; B = possible; C = safe

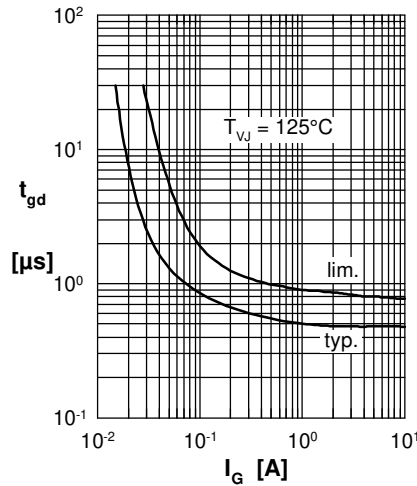


Fig. 5 Gate controlled delay time  $t_{gd}$

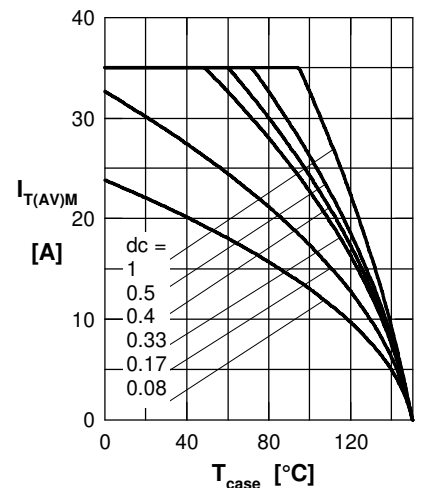


Fig. 6 Max. forward current at case temperature

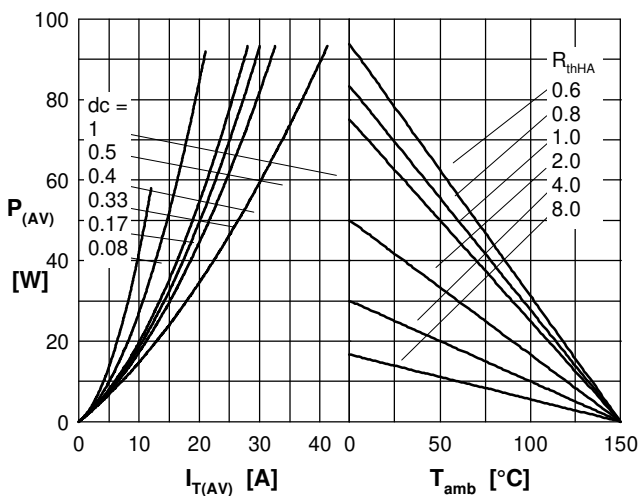


Fig. 7a Power dissipation versus direct output current  
Fig. 7b and ambient temperature

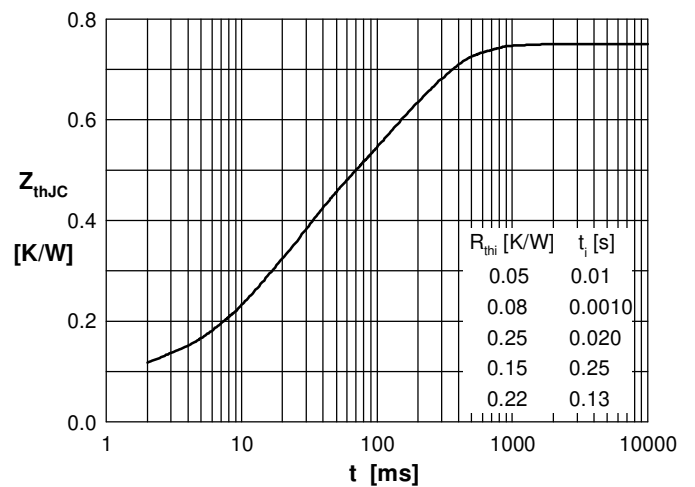


Fig. 7 Transient thermal impedance junction to case